

Specification Amendments

Please replace paragraph 004 with the following re-written paragraph:

[004] A ~~[[C]]~~ cleaning process is widely used after a deposition step. The fell-on particle (particle on deposition surface) after deposition such as metal or oxide layer deposition can be removed by a jet scrubbing method. By using high-pressured de-ionized water, the ~~removal~~ particle on a flat film (deposition surface) will be easily removed.

Please replace paragraph 005 with the following re-written paragraph:

[005] The pressure of de-ionized water can be controlled to ~~keep~~ maintain a particle removal rate by adjusting a jet pump pressure. The higher pressure ~~gets the~~ achieves a better particle removal rate. On the other hand, higher pressure may induce damage on a wafer surface. A limitation pressure is set up to avoid this situation. In order to improve a particle removal rate, extending the process time is the only way to

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achieve ~~the purpose~~ such a goal. Although extending the process time will increase the production duration. A novel jet clean nozzle having multiple spray openings is introduced to provide a high particle removal rate and efficient productivity.